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SEMICONDUCTOR TOSHIBA

TECHNICAL DATA

TOSHIBA PHOTOCOUPLER

TLP181

GaAs IRED & PHOTO - TRANSISTOR

(TLP181)

OFFICE MACHINE

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

TELECOMMUNICATION

The TOSHIBA MINI FLAT COUPLER TLP181 is a small outline coupler, suitable for surface mount assembly.

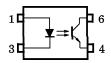
TLP181 consist of a photo transistor optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP package.

Collector-Emitter Voltage : 80V (Min.) Current Transfer Ratio : 50% (Min.) Rank GB : 100% (Min.)

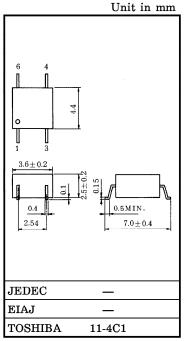
: 3750V_{rms} (Min.) Isolation Voltage

: UL1577, File No. E67349 UL Recognized

PIN CONFIGURATION (TOP VIEW)



1: ANODE 3: CATHODE 4 : EMITTER 6: COLLECTOR



Weight: 0.09g

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SEMICONDUCTOR **TOSHIBA**

TECHNICAL DATA

TLP181

(TLP181)

CURRENT TRANSFER RATIO

TYPE	CLASSI- FICATION	CURRENT TRAN (IC) $I_{\rm F}$ =5mA, V _{CE}	-	MARKING OF CLASSIFICATION	
	*1	MIN.	MAX.		
	(None)	50	600	BLANK, Y, Y [■] , G, G [■] , B, B [■] , GB	
	Rank Y	50	150	Y, Y [■]	
TLP181	Rank GR	100	300	G, G [■]	
	Rank BL	200	600	В, В■	
	Rank GB	100	600	G, G■, B, B■, GB	

*1 : EX, Rank GB : TLP181 (GB)

Note: Application, type neme for certification test, please use standard product type

name, i,e.

TLP181 (GB): TLP181

TLP181 – 2
1996 – 1 – 8
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TECHNICAL DATA

TLP181

(TLP181)

MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT
	Forward Current	$I_{\mathbf{F}}$	50	mA
	Forward Current Detating	$\Delta I_{F} / {}^{\circ}C$	$-0.7 (\mathrm{Ta} \ge 53^{\circ}\mathrm{C})$	mA/°C
LED	Pulse Forward Current	I_{FP}	$1(100\mu\mathrm{s}$ pulse, $100\mathrm{pps})$	A
' '	Reverse Voltage	$V_{\mathbf{R}}$	5	V
	Junction Temperature	T_{j}	125	°C
	Collector-Emitter Voltage	v_{CEO}	80	V
٦ ي	Emitter-Collector Voltage	v_{ECO}	7	V
	Collector Current	$I_{\mathbf{C}}$	50	mA
[E	Collector Power Dissipation (1 Circuit)	PC	150	mW
DETECTOR	Collector Power Dissipation Derating (1 Circuit Ta≥25°C)	ΔP _C /°C	-1.5	mW/°C
	Junction Temperature	T_{j}	125	°C
Sto	rage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C
Оре	erating Temperature Range	$T_{ m opr}$	-55~100	°C
Lea	d Soldering Temperature	T_{sol}	260 (10s)	°C
Tot	al Package Power Dissipation	P_{T}	200	mW
Tot	al Package Power Dissipation Derating (Ta≥25°C)	ΔP _T /°C	-2.0	mW/°C
Isol	ation Voltage (Note 1)	$BV_{\mathbf{S}}$	3750 (AC, 1min., RH≦60%)	V _{rms}

Note 1 Device considered a two-terminal device : Pin 1, 3 shorted together and pins 4, 6 shorted together

TLP181 – 3
1996 – 1 – 8
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TLP181

TECHNICAL DATA

(TLP181)

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC SYMBOL		TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
	Forward Voltage	$V_{\mathbf{F}}$	$I_{\mathbf{F}} = 10 \text{mA}$	1.0	1.15	1.3	V
LED	Reverse Current	$I_{\mathbf{R}}$	I_{R} $V_{R}=5V$		_	10	μ A
	Capacitance	C_{T}	V=0, f=1MHz	_	30		рF
	Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C}\!=\!0.5{\rm mA}$	80	_	_	V
OR	Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	$I_{\text{E}} = 0.1 \text{mA}$	7	_	_	v
DETECTOR	Collector Dark Current	Icno	V _{CE} =48V, (Ambient Light Below 1000 lx)	_	0.01 (2)	0.1 (10)	μ A
DE	Confector Dark Current	ICEO	V _{CE} =48V, Ta=85°C, (Ambient Light Below 1000 lx)	_	2 (4)	50 (50)	μ A
	Capacitance (Collector to Emitter)	CCE	V=0, f=1MHz	_	10	_	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION		TYP.	MAX.	UNIT
Current Transfer Ratio	$I_{ m C}/I_{ m F}$	$I_F = 5mA$, $V_{CE} = 5V$	50	_	600	%
Current Transfer Ratio	10,1k	Rank GB	100	_	600	10
Saturated CTR	I _C / I _{F (sat)}	$I_F = 1mA$, $V_{CE} = 0.4V$	_	60	_	%
Saturated CIR	C'IF (sat)	Rank GB	30	_	_	70
	V _{CE (sat)}	$I_C=2.4mA$, $I_F=8mA$	_		0.4	
Collector-Emitter Saturation Voltage		I_{C} =0.2mA, I_{F} =1mA	_	0.2	_] v
Volume		Rank GB	_	_	0.4	
Off-State Collector Current	I _{C (off)}	$V_{F} = 0.7V, V_{CE} = 48V$	_	1	10	μ A

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	$c_{\mathbf{S}}$	V _S =0V, f=1MHz	_	0.8	_	pF
Isolation Resistance	$R_{\mathbf{S}}$	$V_S = 500V$	5×10^{10}	10^{14}	_	Ω
	$BV_{\mathbf{S}}$	AC, 1 minute	3750	_	_	37
Isolation Voltage		AC, 1 second, in oil	_	10000	_	$V_{ m rms}$
		DC, 1 minute, in oil	_	10000	_	v_{dc}

TLP181 - 4 1996 - 1 - 8 TOSHIBA CORPORATION TECHNICAL DATA

(TLP181)

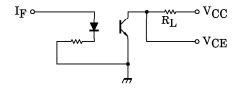
SWICHING CHARACTERISTICS (Ta = 25°C)

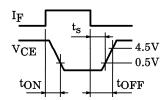
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t _r			2		
Fall Time	t_f	$V_{CC}=10V$, $I_C=2mA$	_	3		
Turn-on Time	ton	$R_L = 100\Omega$		3		μ s
Turn-off Time	t_{off}			3		
Turn-on Time	ton	D 1010(E: 1)	_	2		
Storage Time	t_s	R_L =1.9k Ω (Fig.1) V_{CC} =5V, I _F =16mA	_	25	_	μ s
turn-off Time	$t_{ m OFF}$, CC 3 v, 1 _F 15mm1	_	40	_	

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	v_{CC}	_	5	48	V
Forward Current	$ m I_{ m F}$	1	16	20	mA
Collector Current	$I_{\mathbf{C}}$	_	1	10	mA
Operating Temperature	T_{opr}	-25	_	85	°C

Fig.1 SWITCHING TIME TEST CIRCUIT

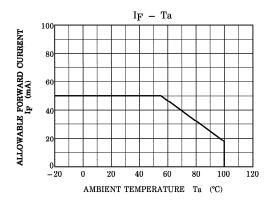


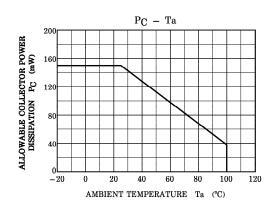


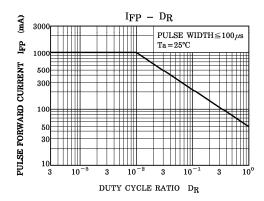
TLP181 – 5
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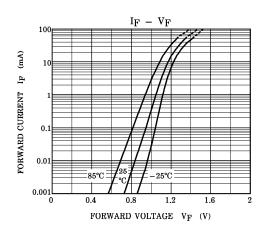
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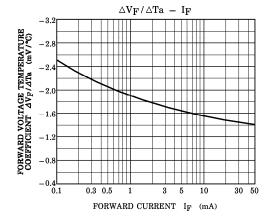
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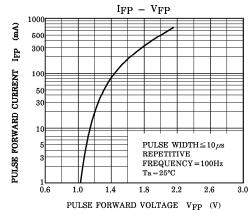












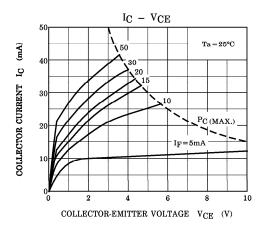
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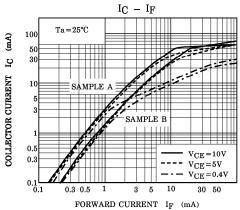
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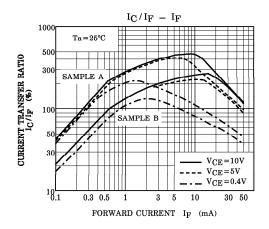
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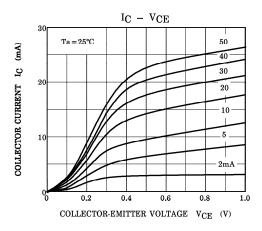
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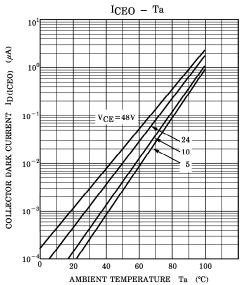
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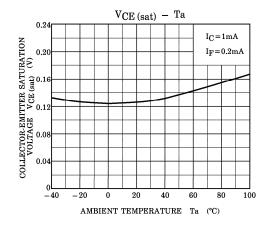


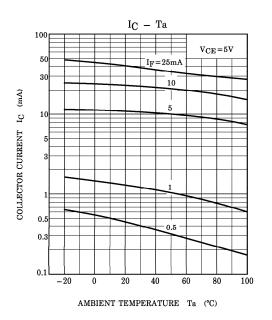


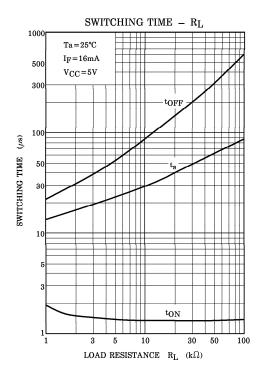
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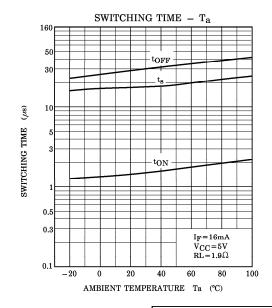
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TLP181 - 8*

1996 - 1 - 8

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